

Abstracts

Model-Extrapolated S-Parameter Design of MM-Wave GaAs FET Amplifiers

L. Dearden, G. Miner and M. Sayed. "Model-Extrapolated S-Parameter Design of MM-Wave GaAs FET Amplifiers." 1986 MTT-S International Microwave Symposium Digest 86.1 (1986 [MWSYM]): 385-388.

Broadband millimeter-wave GaAs MESFET amplifiers have been designed from model-extrapolated S-parameters. An equivalent circuit MESFET model valid to 40 GHz is given. Amplifier performance from 15-50 GHz is shown and compared with the equivalent circuit model.

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